

Computer Organization & Architecture

## 3-2 Semiconductor Static RAM

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# Contents of this lecture

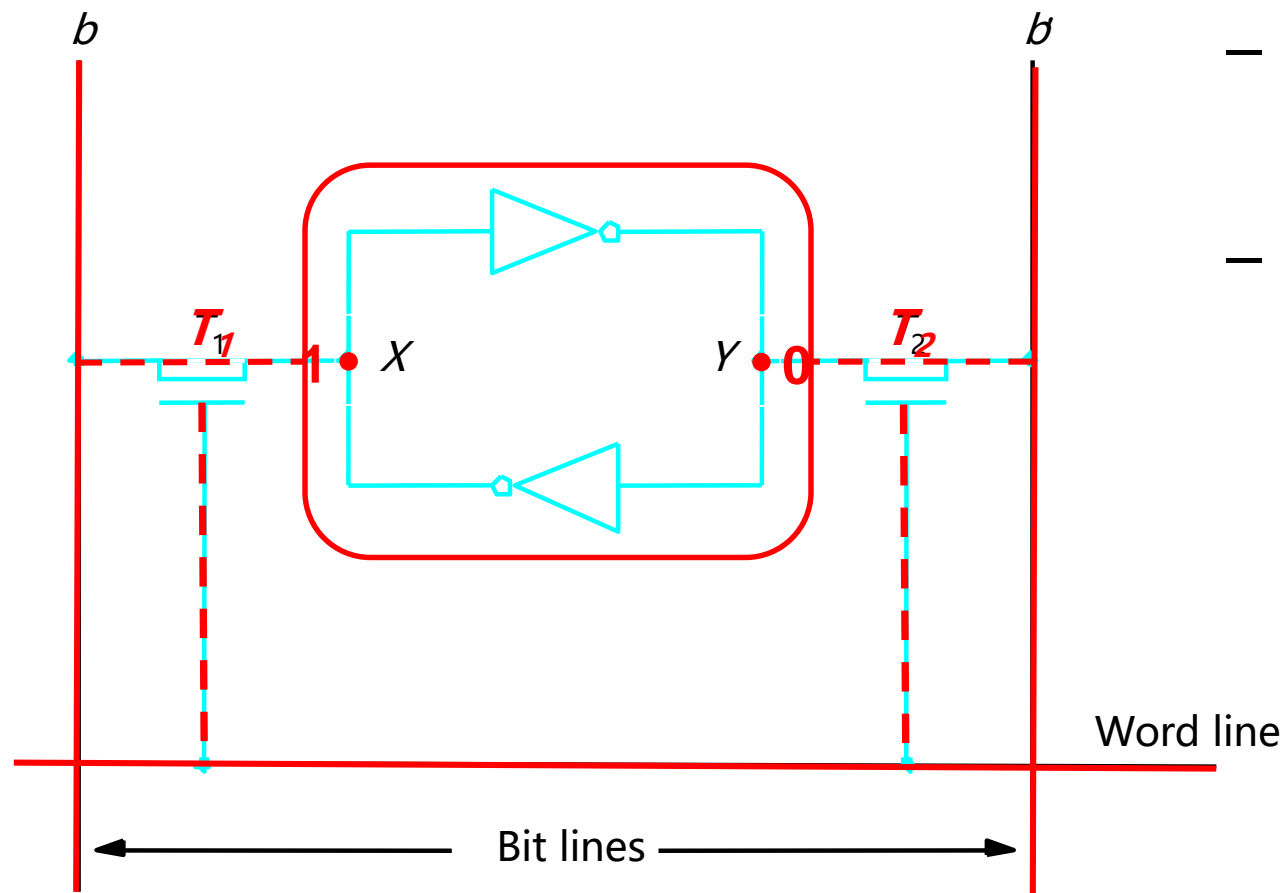
- Static RAM Cell
- Organization of Static RAM Chips

# RAM Technology

- Static Technology
  - In a static RAM, binary values are stored using traditional flip-flop logic-gate configurations.
- Dynamic Technology
  - A dynamic RAM is made with cells that store data as charge on capacitors. The presence or absence of charge in a capacitor is interpreted as a binary 1 or 0.

# Static RAM (SRAM) Cell (1)

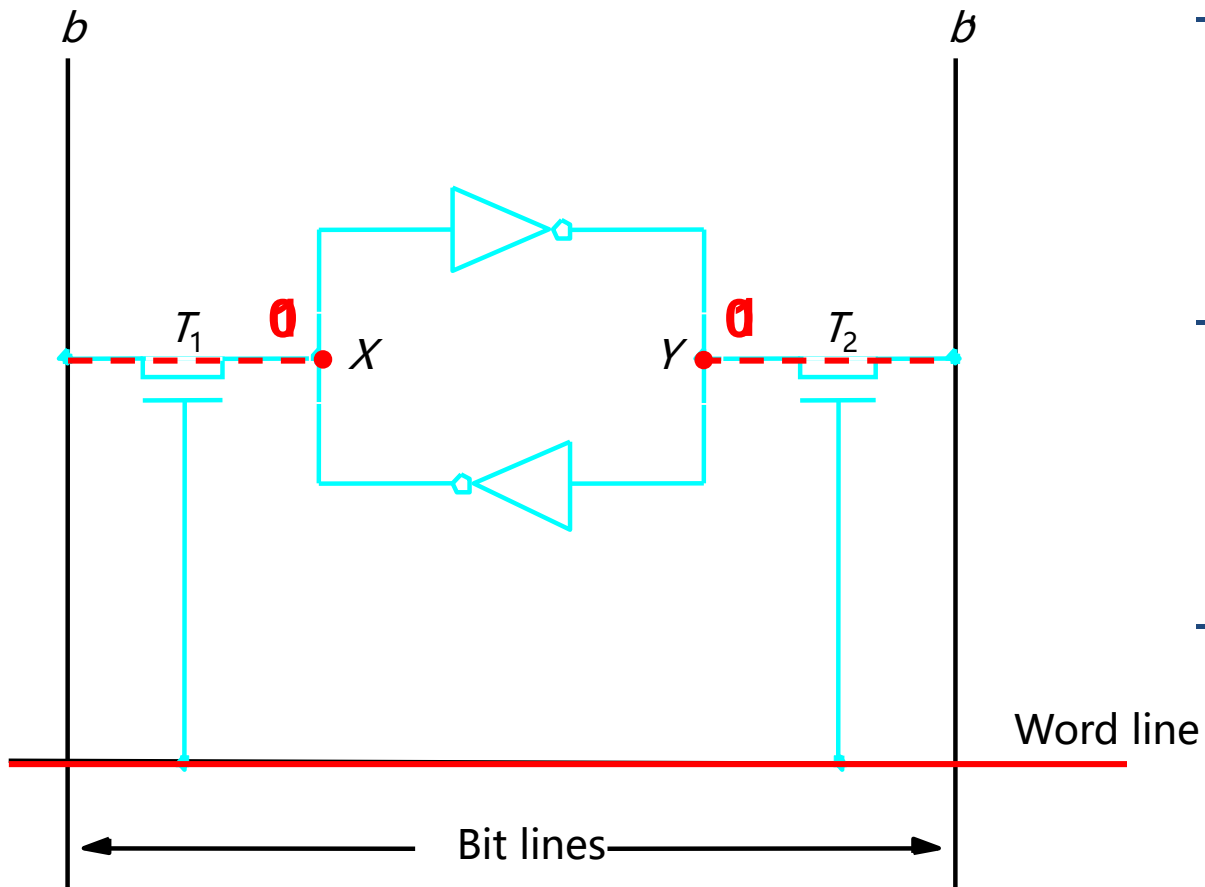
- Implementation of a SRAM cell



- Maintain State
  - The word line is at low level
- Assume that the cell is in state 1 if the logic value at point X is 1 and at point Y is 0.

# SRAM Cell (2)

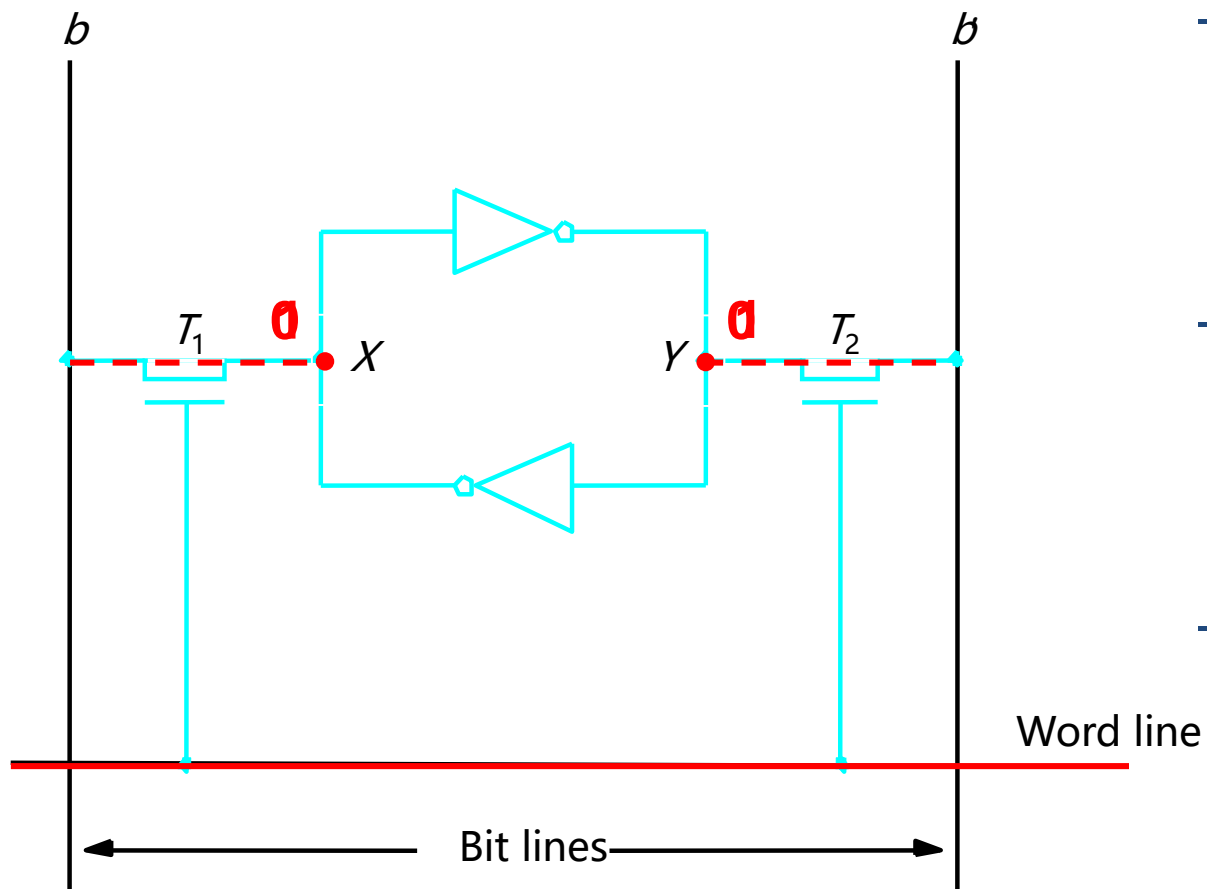
- Read Operation



- The word line is at high level.
- Read “1”: The signal on the bit line  $b$  is high and the signal on the bit line  $b'$  is low.
- Read “0”: The signal on the bit line  $b$  is low and the signal on the bit line  $b'$  is high.
- Note: Sense/write circuits at the end of the bit lines monitor the state of  $b$  and  $b'$  and set the output accordingly.

# SRAM Cell (3)

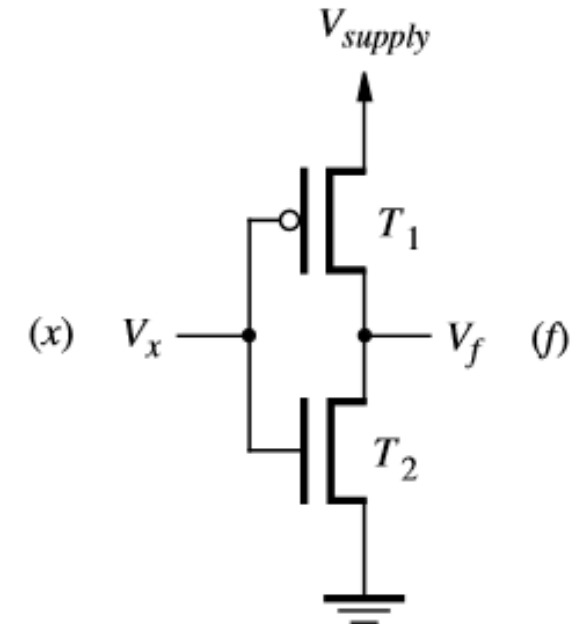
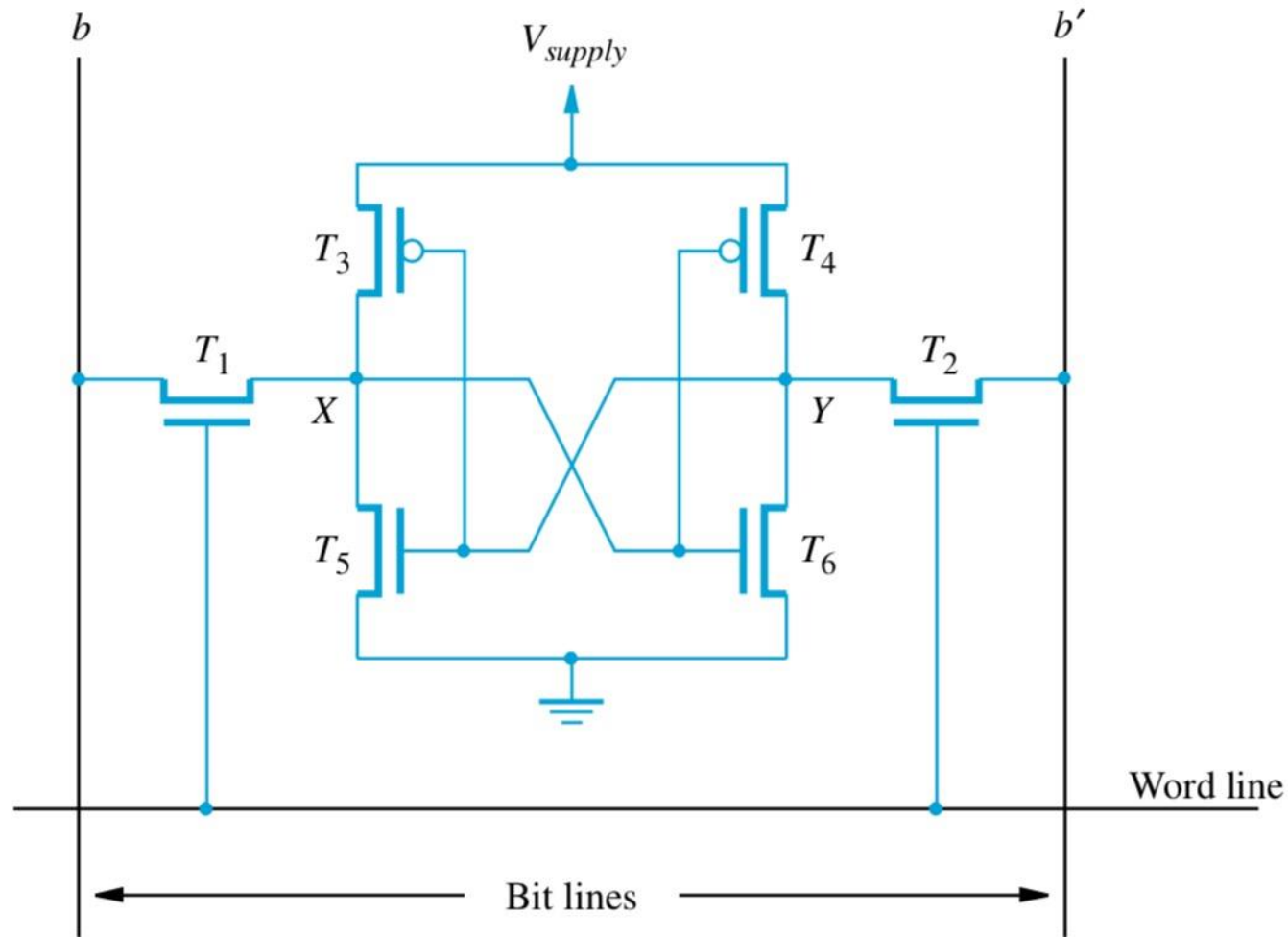
- Write Operation



- The word line is at high level.
- **Write “1”** : Place high level signal on bit line  $b$  and place low level signal on bit line  $b'$ .
- **Write “0”** : Place low level signal on bit line  $b$  and place high level signal on bit line  $b'$ .
- **Note**: The required signals on the bit lines are generated by the Sense/Write circuit.

# SRAM Cell (4)

- CMOS Realization of a SRAM cell



$x$	$V_x$	$T_1$	$T_2$	$V_f$	$f$
0	low	on	off	high	1
1	high	off	on	low	0

# SRAM Cell (5)

- CMOS Realization of a SRAM cell
  - The power supply voltage is 5V in older CMOS SRAMs or 3.3V in new low-voltage versions.
  - If power is interrupted and then it is restored, the latch will settle into a stable state, but it will not necessarily be the same state the cell was in before the interruption.
  - CMOS SRAMs' power consumption is very low.

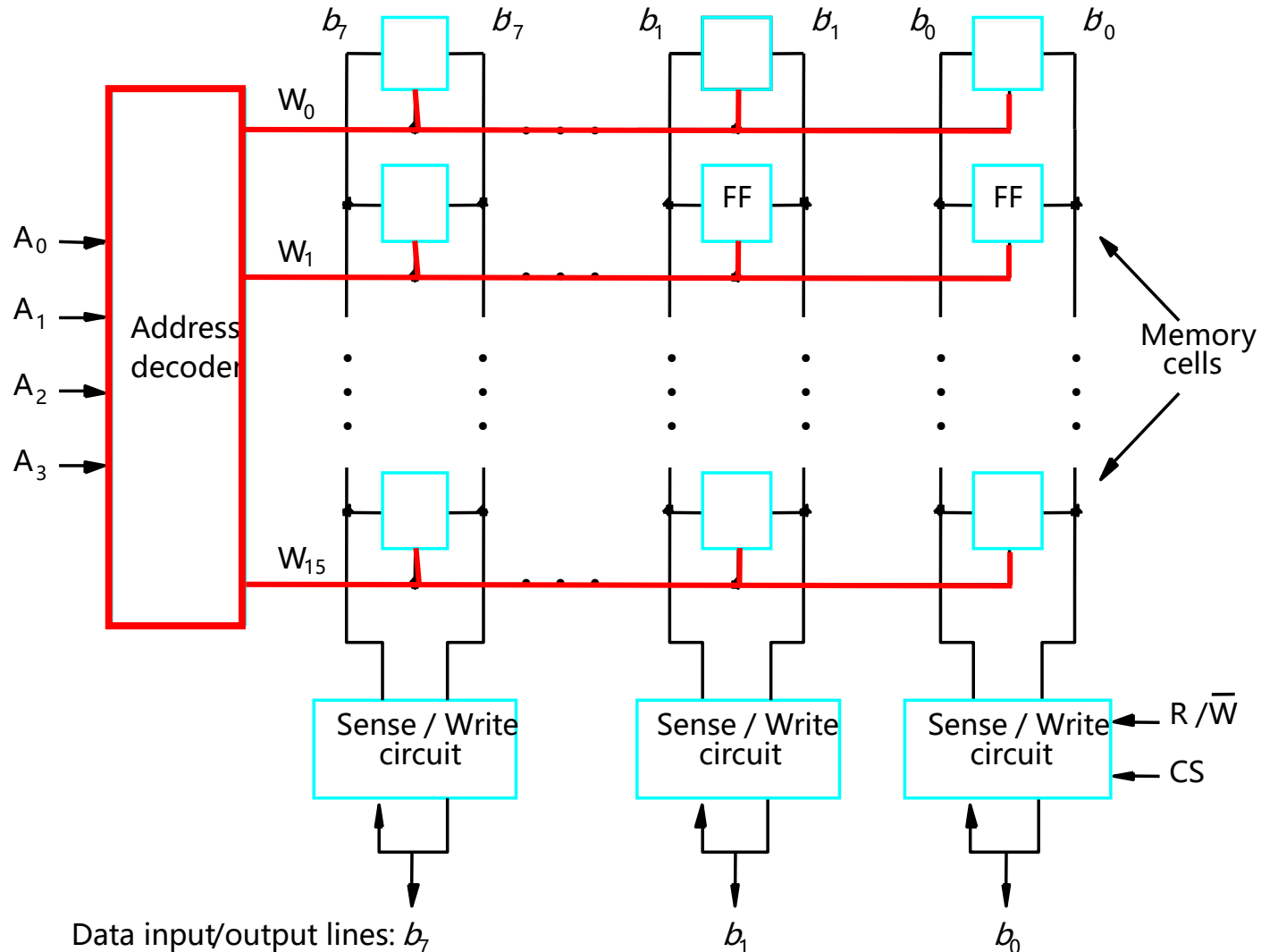


# SRAM Cell (6)

- Advantage and Disadvantage of SRAM
  - Advantage: Fast
  - Disadvantage: Low density, High cost

# Organization of SRAM Chips (1)

- Organization of 128 Bit Cells ( $16 \times 8$ )

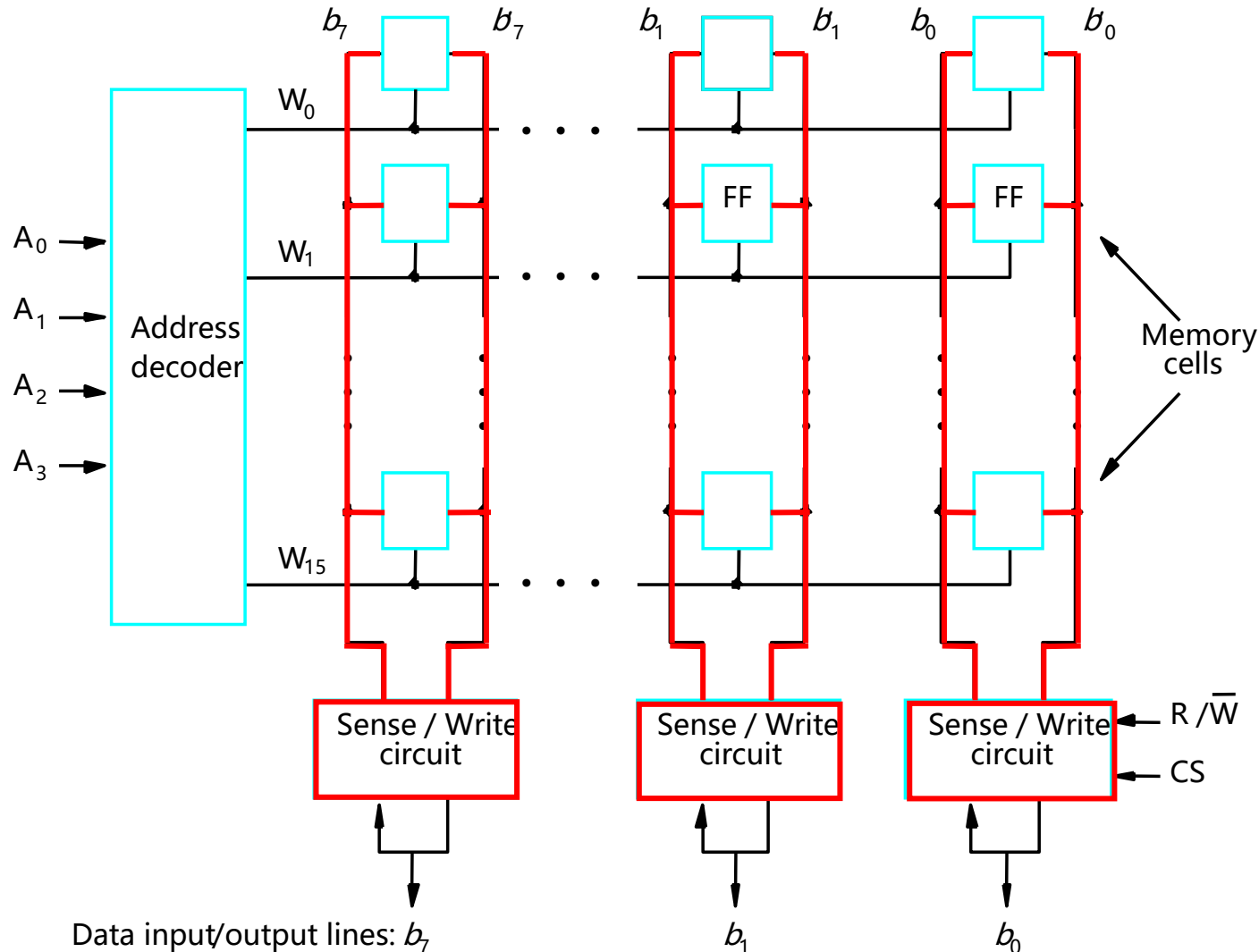


- Internal Organization

- Word line:** All cells of a row are connected to the word line. It is driven by the address decoder.

# Organization of SRAM Chips (2)

- Organization of 128 Bit Cells ( $16 \times 8$ )

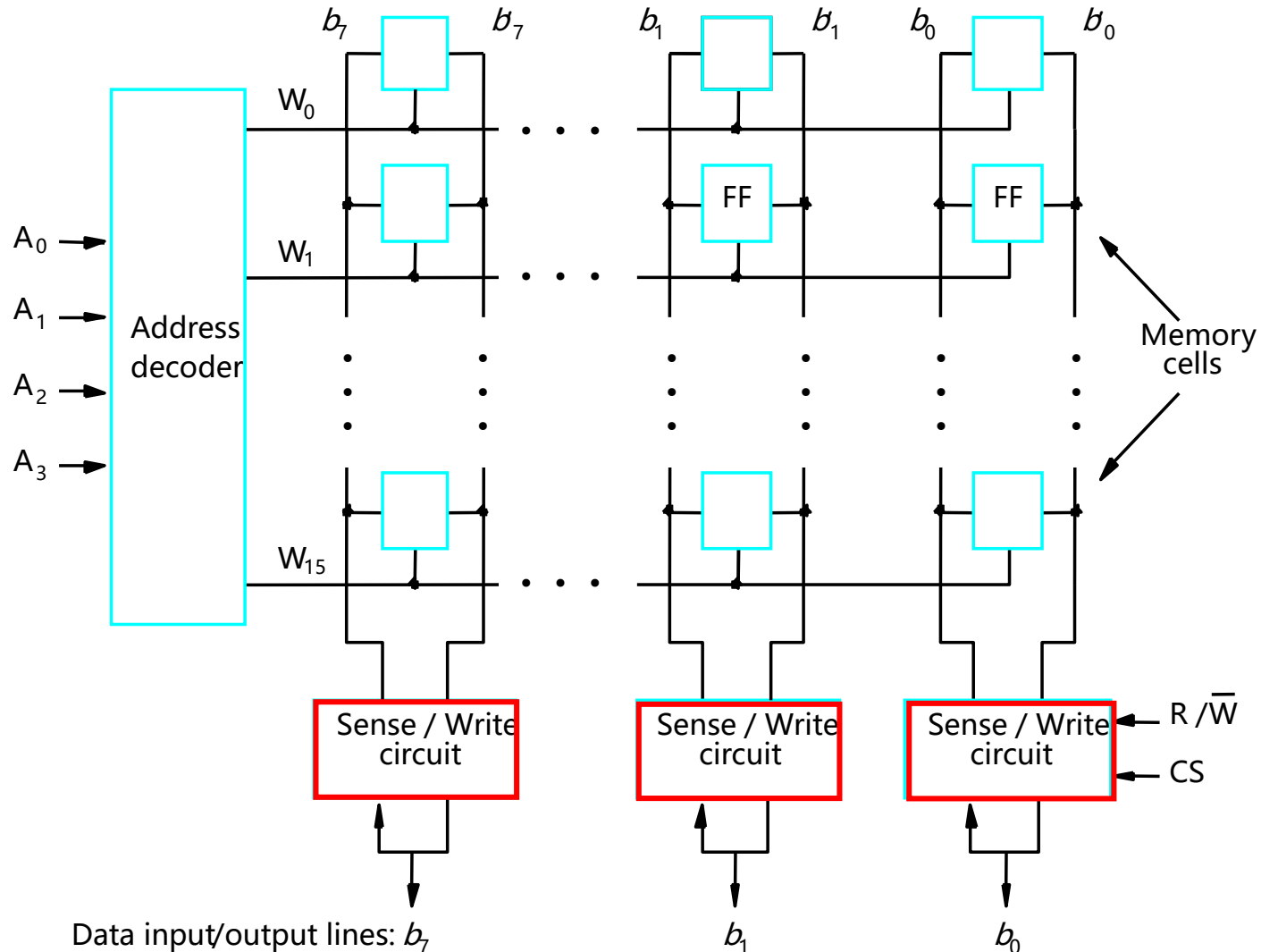


- Internal Organization

- Bit lines:** The cells in each column are connected to a Sense/Write circuit by two bit lines.

# Organization of SRAM Chips (3)

- Organization of 128 Bit Cells ( $16 \times 8$ )



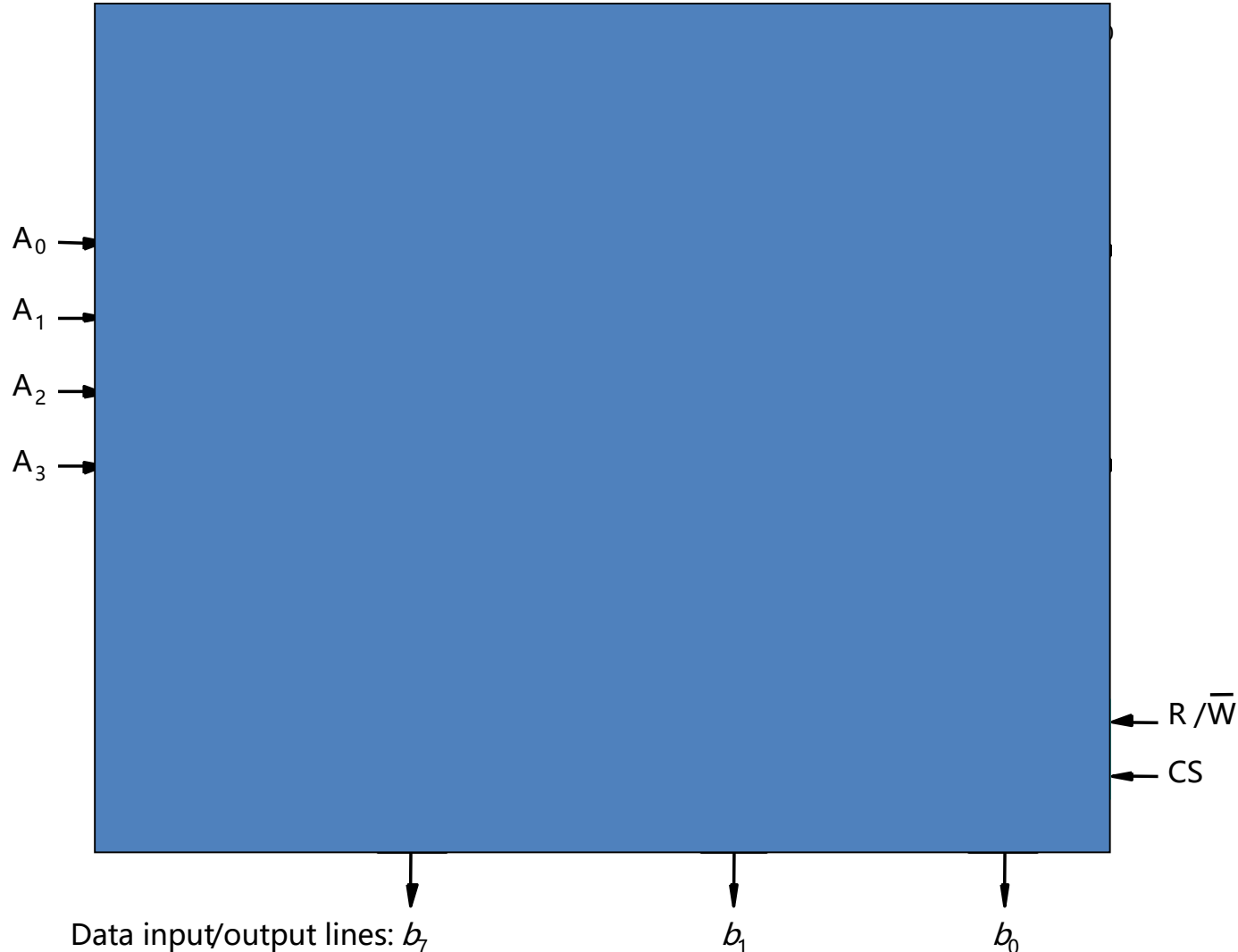
- Internal Organization

- Sense/Write circuits**

- Read: They sense the information stored in the cells selected by a word line and transmit this information to the output data lines.
    - Write: They receive input information and store it in the cells of the selected word

# Organization of SRAM Chips (4)

- Organization of 128 Bit Cells ( $16 \times 8$ )



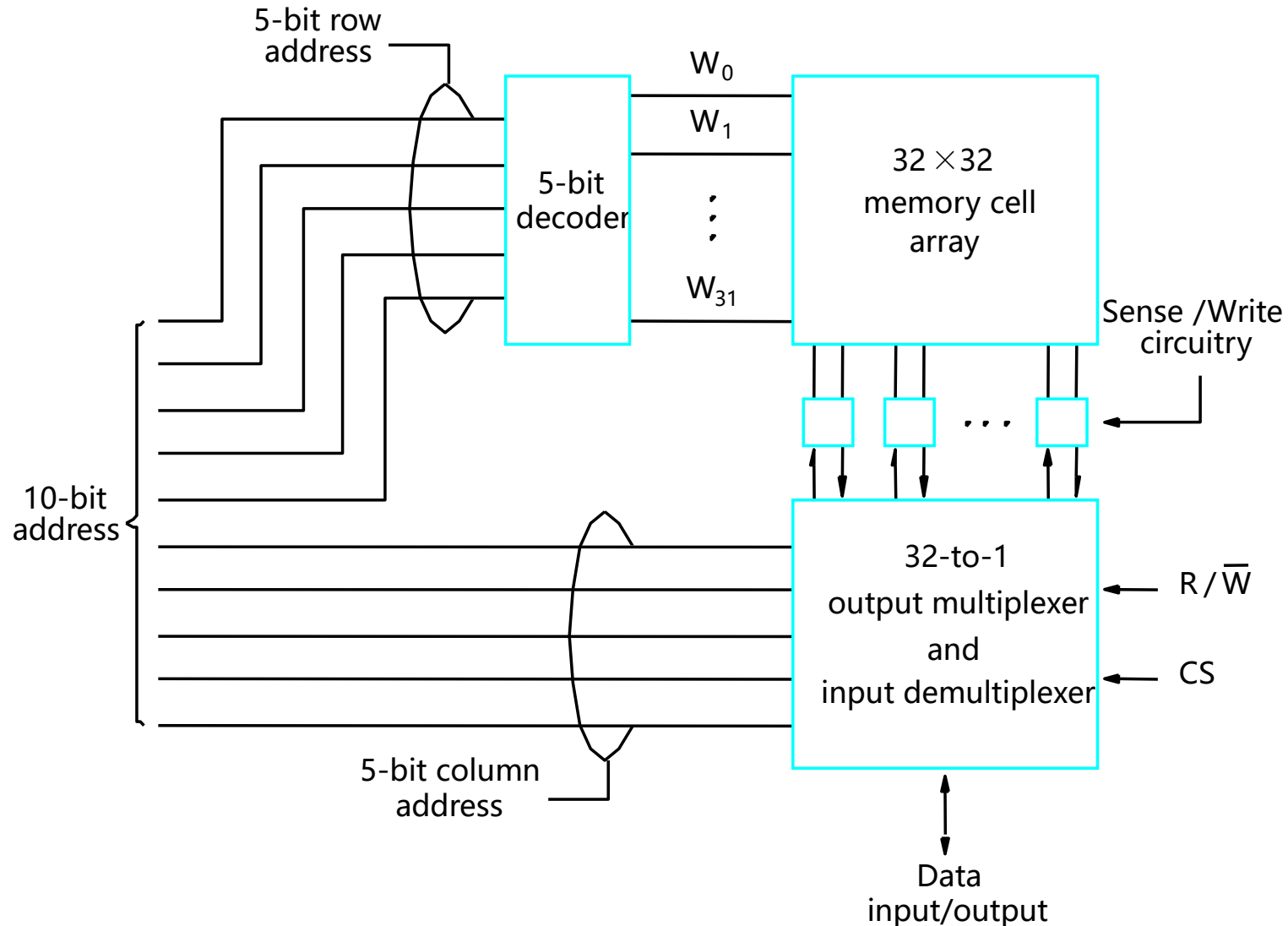
- External Organization

- Address lines (Input ):  $A_0 - A_3$
    - Data lines (Input/Output ):  $b_0 - b_7$
    - Control lines(Input)
      - R/W (Read/Write): Specify the required Read or Write operation.
      - CS (Chip Select): Select a given chip in a multi-chip memory system.
    - Power Supply line
    - Ground line
    - Total Connections =  $4 + 8 + 2 + 1 + 1$

$$= 16$$

# Organization of SRAM Chips (5)

- Organization of 1024 Bit Cells ( $1K \times 1$ )



# Organization of SRAM Chips (6)

- Organization of 1024 Bit Cells ( $1K \times 1$ )
  - External Organization
    - Address lines (Input ):  $A_0 - A_9$
    - Data lines (Input/Output ):  $b_0$
    - Control lines(Input): R/W, CS
    - Power Supply line
    - Ground line
    - Total Connections =  $10 + 1 + 2 + 1 + 1 = 15$

# Quiz (1)

1. Assume that the capacity of a kind of SRAM chip is  $8K \times 16$ , so the address lines and data lines of this chip are \_\_\_\_\_ respectively.  
A. 8,16    B. 13,16    C. 13,4    D. 8,4
2. Assume that the capacity of a kind of SRAM chip is  $32K \times 32$ , so the sum of address lines and data lines of this chip is \_\_\_\_\_.  
A. 47    B. 64    C. 46    D. 74



# Quiz (2)

3. What are the advantage and disadvantage of SRAM?

Advantage: Fast

Disadvantage: Low density, High cost